Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.   (currently amended) A fabricating method of a semiconductor device comprising:

(a) forming a film which to form a pattern on a structure of a semiconductor substrate;

(b) forming an anti-reflection layer on the film to form a stacking structure including the film and the anti-reflection layer;

(c) performing a plasma treatment to form a plurality of adjacent grooves on an upper surface of the stacking structure, wherein the grooves are configured to increase adhesion between the upper surface of the stacking structure and a photoresist layer;

(d) forming a photoresist pattern on the stacking structure on which the grooves are formed; and

(e) etching the stacking structure using the photoresist pattern as a mask to form a stacking structure pattern.

2.   (original) The method of claim 1, wherein performing the plasma treatment includes performing the plasma treatment for 15-30 seconds using N_2O plasma.

3.   (currently amended) The method of claim 1, wherein forming the photoresist [[patterin]] pattern includes applying a photoresist layer, exposing the photoresist layer to a light selectively, and developing the photoresist layer to form the photoresist pattern exposing a part of the stacking structure.

4.   (original) The method of claim 3, wherein a far ultraviolet ray is used as a light source in exposing the photoresist layer to a light selectively.

5.   (original) The method of claim 1, wherein a SiO_xN_y layer having thickness of 200~300Å is used as the anti-reflection layer.

6.   (original) The method of claim 1, wherein the film is a metal film.

7.   (original) The method of claim 1, wherein forming the antireflection layer includes forming a protective oxide layer on the anti-reflection layer after forming the anti-reflection layer to form a stacking structure including the film, the anti-reflection layer, and the protective oxide layer.

8.   (original) The method of claim 7, wherein the protective oxide layer is formed to have thickness of equal to or less than 100Å.

9.   (original) The method of claim 7, wherein the plasma treatment is performed for 15-30 seconds using N_2O plasma.

10.   (original) The method of claim 7, wherein a SiO_xN_y layer having thickness of 200~300Å is used as the anti-reflection layer.

11.   (original) The method of claim 7, wherein the film is a metal film.

Claims 12-20 (canceled)

21.   (new) A fabricating method of a semiconductor device comprising:

(a) forming a film which to form a pattern on a structure of a semiconductor substrate;

(b) forming an anti-reflection layer on the film;

(c) forming a protective oxide layer on the anti-reflection layer after forming the anti-reflection layer to form a stacking structure including the film, the anti-reflection layer, and the protective oxide layer;

(d) performing a plasma treatment to form grooves on an upper surface of the stacking structure;

(e) forming a photoresist pattern on the stacking structure on which the grooves are formed; and

(f) etching the stacking structure using the photoresist pattern as a mask to form a stacking structure pattern.

22.   (new) The method of claim 21, wherein the protective oxide layer is formed to have thickness of equal to or less than 100Å.

23.   (new) The method of claim 21, wherein the plasma treatment is performed for 15-30 seconds using N_2O plasma.

24.   (new) The method of claim 21, wherein a SiO_xN_y layer having thickness of 200~300Å is used as the anti-reflection layer.

25.   (new) The method of claim 21, wherein the film is a metal film.

Amendments to the Drawings:

The attached replacement sheet of drawing includes changes to FIG. 1. This replacement sheet, which includes FIGS. 1 and 2, replaces the original sheet including FIGS. 1 and 2. The attached annotated sheet shows changes to FIG. 1 in red ink. In amended FIG. 1, the previously omitted descriptive legend "(Prior Art)" has been added.

Attachment: Replacement Sheet

Annotated Sheet Showing Changes